



Title of Change:	NCV7471 Datasheet Update – Revision 3		
Effective date:	20 August 2015		
Contact information:	Contact your local ON Semiconductor Sales Office or <Roman.Buzas@onsemi.com>		
Type of notification:	ON Semiconductor will consider this change accepted.		
Change category:	☐ Wafer Fab Change ☐ Assembly Change ☐ Test Change ☒ Other		
Change Sub-Category(s): ☐ Manufacturing Site Change/Addition ☐ Manufacturing Process Change ☐ Material Change ☐ Product specific change ☒ Datasheet/Product Doc change ☐ Shipping/Packaging/Marking ☐ Other: _____			
Sites Affected: ☐ All site(s) ☒ not applicable ☐ ON Semiconductor site(s) : ☐ External Foundry/Subcon site(s)			
Description and Purpose: - Functional Description: - VOUT failure description updated (Page 26) - Thermal Characteristics added: - Junction-to-Case thermal resistance parameter added (Page 37) - Electrical Characteristics tables updated: - Io(SC)(CANL) test condition fixed (Page 42) - Rpulldown_pinx parameter name fixed (Page 47) - V_FSOx_active defined newly for I(FSOx) = 10 mA (Page 48) - Vhys_WU limits changed to 0.03 – 0.25 V (Page 48)			
List of affected Standard Parts: NCV7471DQ5G NCV7471DQ5R2G			